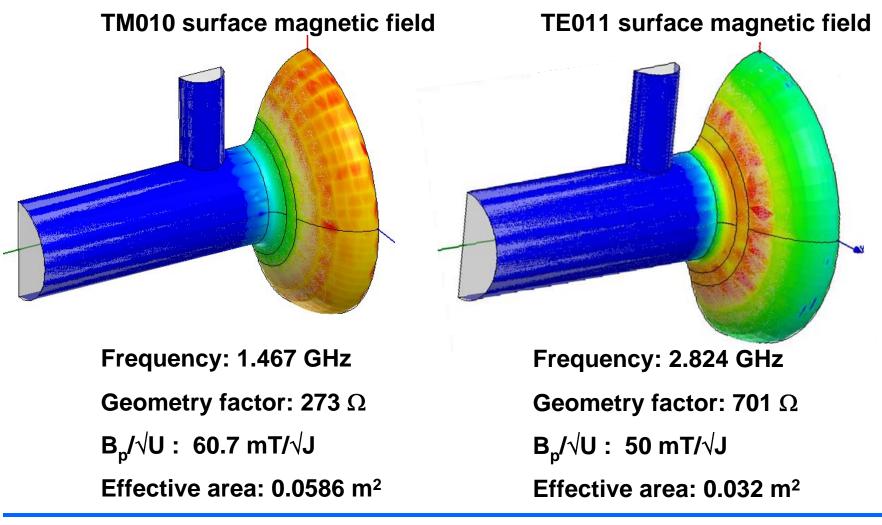
Measurements of the high field Q-drop in TE011/TM010 in a single cell cavity

Gianluigi Ciovati Jefferson Lab

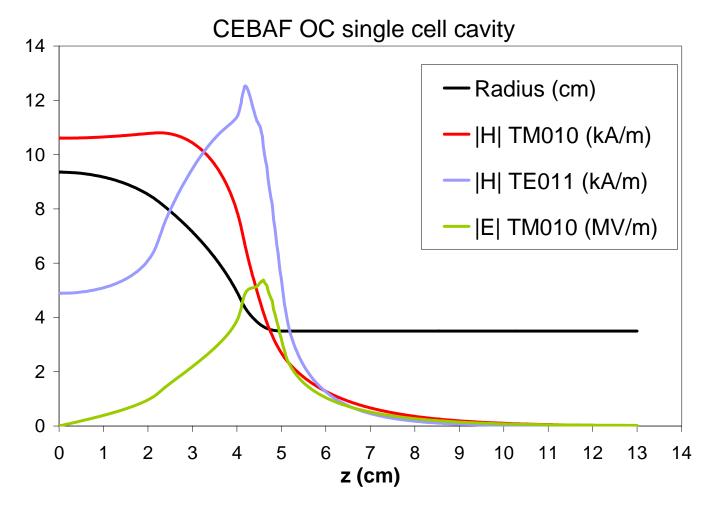


TE011 vs. TM010 properties





Surface fields distribution



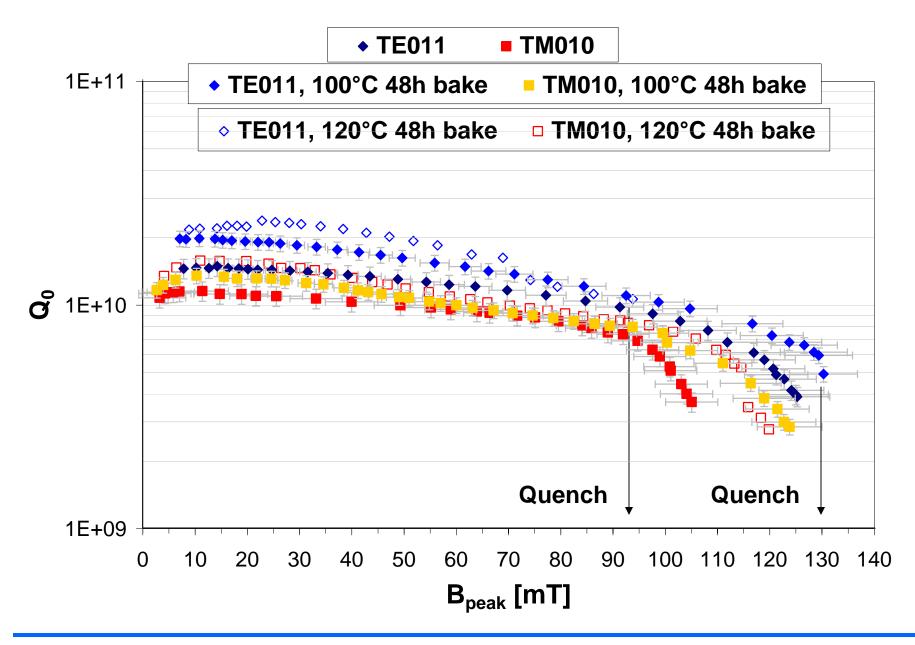
TE011 has no electric field on the cavity surface



Cavity preparation & test

- Degreasing
- 20 µm BCP 1:1:1 or 1:1:2
- 1 h HPR
- Dried overnight in clean room class 10
- Assembly in clean room class 10
- Rs vs. T measured from 4.2 K to 1.8 K
- Q_0 vs. B_{peak} measured at 2 K in both modes







Thermal model

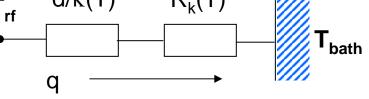
rf surface temperature vs. B_p obtained:

$$R_{s}(T) = \frac{A}{T} \ln\left(\frac{4kT}{hf}\right) e^{-B/T} + R_{res} \qquad \text{A, B, } R_{res} \text{ from } R_{s} \text{ vs. T fit}$$

fit with R_s data obtained from high power test

AND...

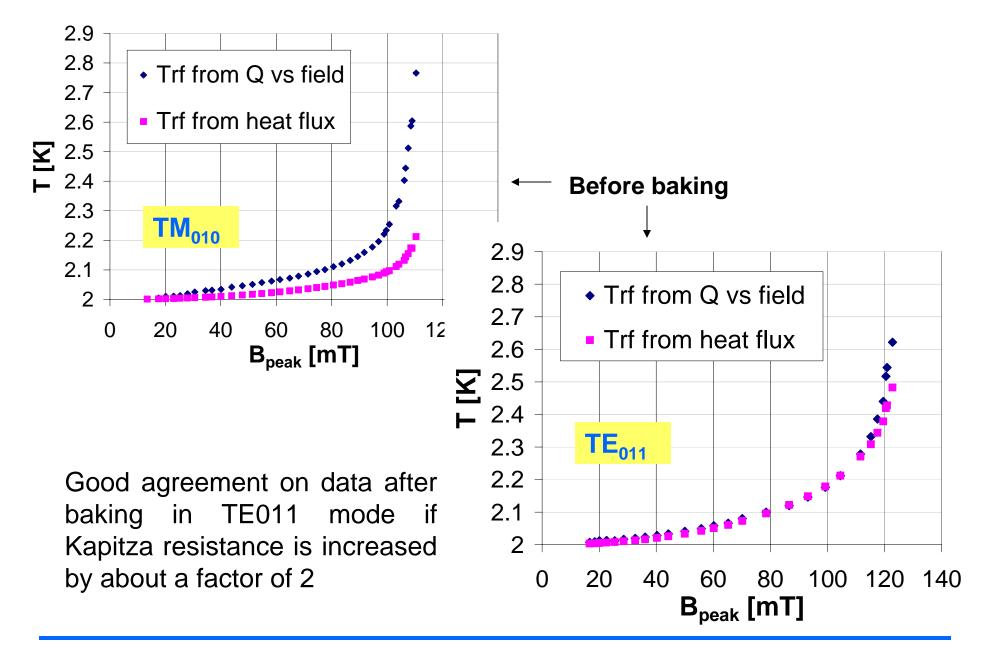
- Heat flux $q = P_c / A_{eff}$
- Thermal conductivity and Kapitza resistance for Nb RRR=200 from published data⁺ T_{rf} d/k(T) R_k(T)



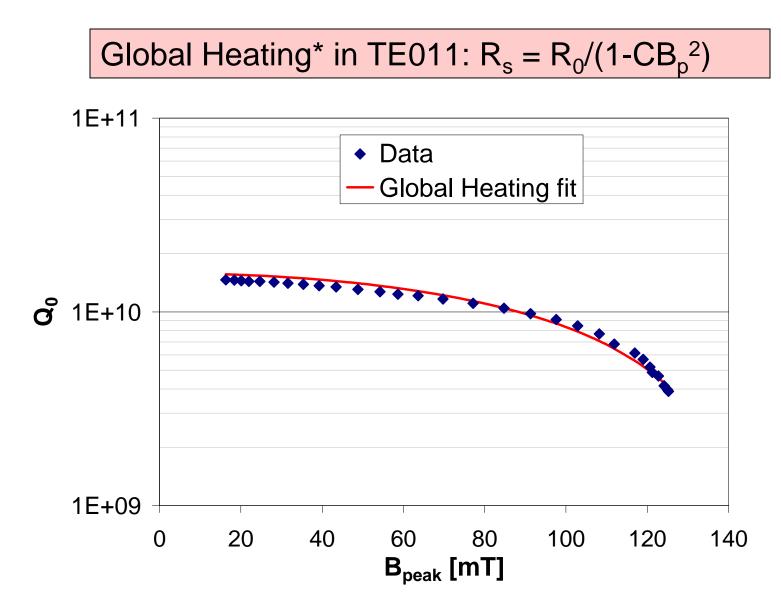
[†]A. Boucheffa et al., *Cryogenics* **34**, 297 (1994)

S. Bousson, et al, Proc. 9th Workshop on RF Supercond., Santa Fe, USA (1999)





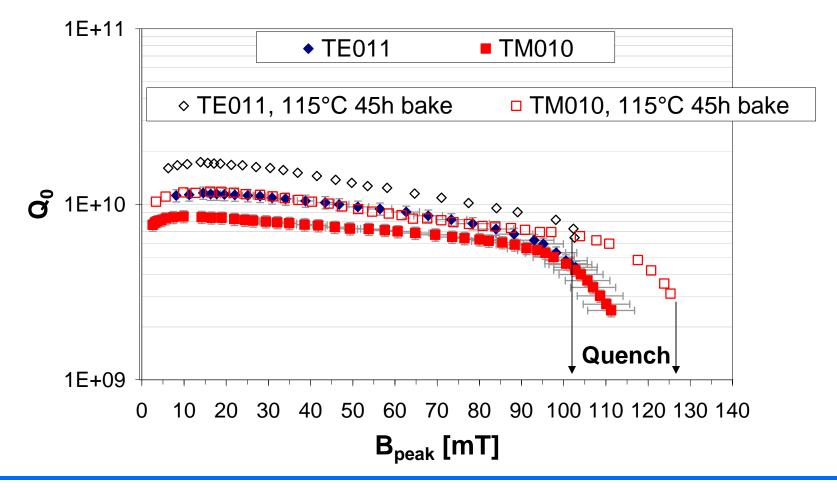




*B. Visentin et al, Proc. 9th Workshop on RF Supercond., Santa Fe, USA (1999)

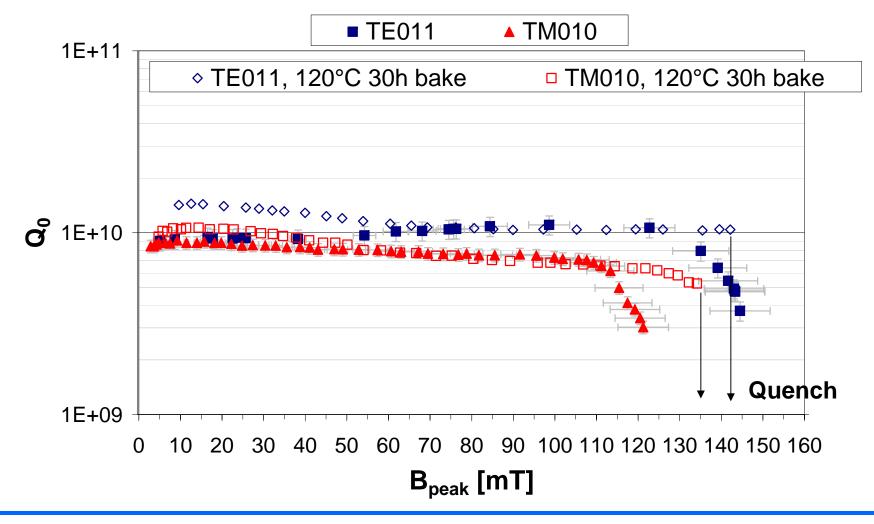


Anodization: 90 nm thick oxide layer growth after chemical etch



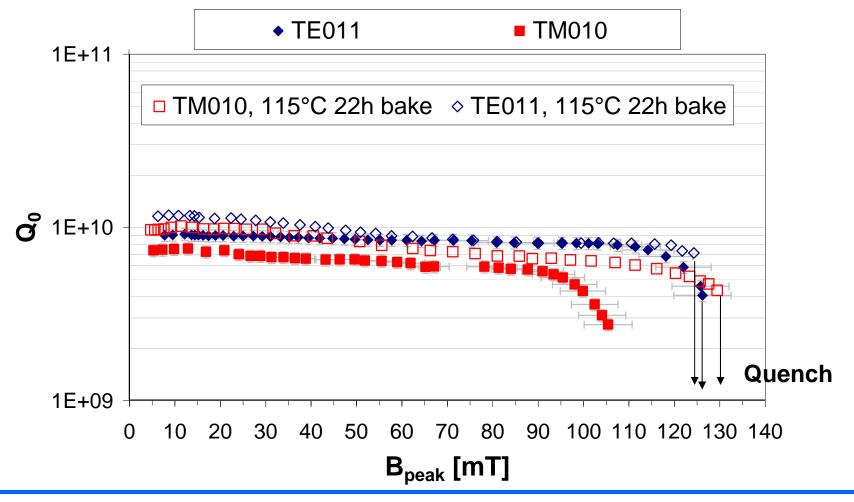


Heat treatment: 1250°C, 12h ramp down to 1000°C in 20h. RRR improved from 320 to 725 measured on sample



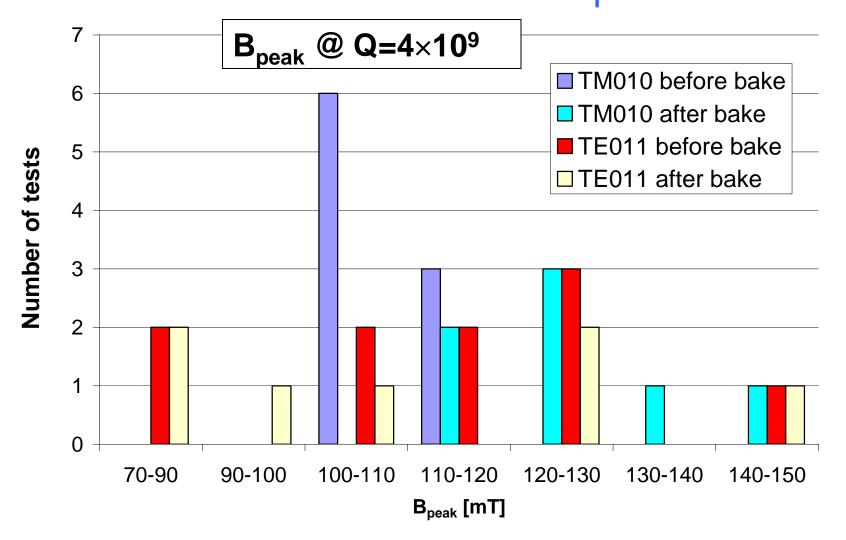


- Global heating model less accurate in describing high field Q-drop after heat treatment in TE mode.
- Surface resistance increases exponentially as in TM mode





Summary of Q vs. B_p results





Influence of treatments on Q-drop

- Baking at 120°C
 - Same Q-drop improvement for 48, 30, 22, 12h
- After HT (larger grains, higher thermal conduct.):
 - No changes in Q-drop features in TM mode
 - Exponentially decreasing Q appears in TE mode (as in TM mode)
- After anodization:
 - Smoother Q-drop in TM mode
 - Max field in TE mode < TM mode</p>



Medium field Q-slope results

	γ values	TM010	TE011
Before HT {	Before bake	2.5	2.6
	After bake*	3.1	3.3
After HT {	Before bake	1.0	0.6
	After bake*	1.9	1.8

* After baking the $R_{\rm s}$ vs. $B_{\rm p}$ dependence change from quadratic to linear



Material parameters results

After baking:

- Small increase (< 5%) of Δ
- Decrease of m.f.p. *l* to ~ 25-40 nm
- Increase of **R**_{res}

	TM010	TE011
before bake	$6 n\Omega$	$9\mathrm{n}\Omega$
after bake	12 nΩ	$11\mathrm{n}\Omega$



Q-drop discussion

- Magnetic field enhancement model (MFE) ⁽¹⁾
 Q-drop due to surface roughness yielding magnetic field enhancement local quenches lowering Q
- Interface tunnel exchange model (ITE) ⁽²⁾

Q-drop due to exponentially increasing surface resistance due to e⁻ tunneling from localized states at Nb-oxide interface under E field

(1) J. Knobloch et al, *Proc. 9th Workshop on RF Supercond.,* Santa Fe, USA (1999)

(2) J. Halbritter, IEEE Trans. On Appl. Superc., 11 No 1, 1864 (2001)

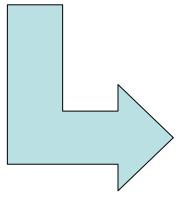


- Max. field before baking is higher in TE mode than TM mode
 - MFE model: B-field in TM mode is high in the equator weld area where there are larger steps
 - ITE model: Q-drop in TM mode is dominated by the E-field
- Q-drop improvement after baking, limited by quench
 - MFE model: increase of B_{sh} due to O diffusion (not supported by measurements)
 - ITE model: reduction of density of localized states for TM mode, no explanation for TE mode



Conclusion

• The same dependence R_s vs. B_p as seen in TM010 mode above 90mT was observed in TE011 mode at higher field, once the thermal conduc. was decreased by HT



- Q-drop is more probable to be a magnetic field effect
- None of the present models explain all the experimental results

